

ABSTRACT OF THE DISCLOSURE

A storage-type SiC-MISFET includes a SiC substrate, an n-type drift layer, a p-type well region, an n-type source region, a SiC channel layer which contains an n-type impurity and is to be a storage-type channel layer, a p-type heavily doped contact layer, a
5 gate insulation film, a gate electrode and the like. In the storage-type SiC-MISFET, a partially heavily doped layer is formed by partially implanting ions of a p-type impurity into an upper surface portion of the n-type drift layer and containing an impurity of the same conductive type as that of the impurity implanted into the well region at a higher concentration than that in the well region.